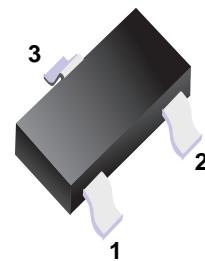


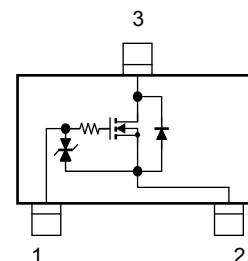
■ N-Channel MOSFET

■ FEATURES

- 1.5-V drive
- Low ON-resistance : $R_{on} = 1.52 \Omega$ (max) (@ $V_{GS} = 1.5$ V)
 : $R_{on} = 1.14 \Omega$ (max) (@ $V_{GS} = 1.8$ V)
 : $R_{on} = 0.85 \Omega$ (max) (@ $V_{GS} = 2.5$ V)
 : $R_{on} = 0.66 \Omega$ (max) (@ $V_{GS} = 4.5$ V)
 : $R_{on} = 0.63 \Omega$ (max) (@ $V_{GS} = 5.0$ V)



■ Simplified outline(SOT-523)



■ Equivalent Circuit (top view)

■ Absolute Maximum Ratings ($T_a = 25$ °C)

Characteristics		Symbol	Rating	Unit
Drain-source voltage		V_{DS}	20	V
Gate-source voltage		V_{GSS}	± 10	V
Drain current	DC	I_D	500	mA
	Pulse	I_{DP}	1000	
Drain power dissipation		P_D (Note1)	150	mW
Channel temperature		T_{ch}	150	°C
Storage temperature range		T_{stg}	-55 to 150	°C

Note1: Mounted on an FR4 board
 (25.4 mm × 25.4 mm × 1.6 mm, Cu Pad: 0.36 mm² × 3)

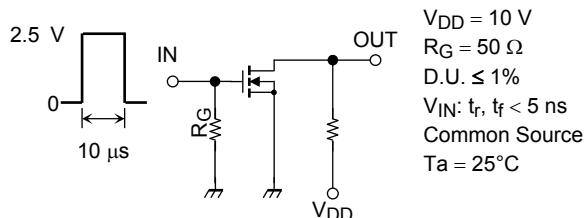
■ Electrical Characteristics ($T_a = 25^\circ\text{C}$)

Characteristics	Symbol	Test Conditions	Min	Typ.	Max	Unit	
Drain-source breakdown voltage	$V_{(\text{BR}) \text{ DSS}}$	$I_D = 1 \text{ mA}, V_{GS} = 0$	20	—	—	V	
	$V_{(\text{BR}) \text{ DSX}}$	$I_D = 1 \text{ mA}, V_{GS} = -10 \text{ V}$	12	—	—		
Drain cutoff current	I_{DSS}	$V_{DS} = 20 \text{ V}, V_{GS} = 0$	—	—	1	μA	
Gate leakage current	I_{GSS}	$V_{GS} = \pm 10 \text{ V}, V_{DS} = 0$	—	—	± 1	μA	
Gate threshold voltage	V_{th}	$V_{DS} = 3 \text{ V}, I_D = 1 \text{ mA}$	0.35	—	1.0	V	
Forward transfer admittance	$ Y_{fs} $	$V_{DS} = 3 \text{ V}, I_D = 200 \text{ mA}$ (Note2)	420	840	—	mS	
Drain-source ON-resistance	$R_{DS (\text{ON})}$	$I_D = 200 \text{ mA}, V_{GS} = 5.0 \text{ V}$ (Note2)	—	0.46	0.63	Ω	
		$I_D = 200 \text{ mA}, V_{GS} = 4.5 \text{ V}$ (Note2)	—	0.51	0.66		
		$I_D = 200 \text{ mA}, V_{GS} = 2.5 \text{ V}$ (Note2)	—	0.66	0.85		
		$I_D = 100 \text{ mA}, V_{GS} = 1.8 \text{ V}$ (Note2)	—	0.81	1.14		
		$I_D = 50 \text{ mA}, V_{GS} = 1.5 \text{ V}$ (Note2)	—	0.95	1.52		
Input capacitance	C_{iss}	$V_{DS} = 10 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$	—	46	—	pF	
Output capacitance	C_{oss}		—	10.8	—		
Reverse transfer capacitance	C_{rss}		—	7.3	—		
Total Gate Charge	Q_g	$V_{DS} = 10 \text{ V}, I_D = 0.5 \text{ A}$ $V_{GS} = 4.0 \text{ V}$	—	1.23	—	nC	
Gate-Source Charge	Q_{gs}		—	0.60	—		
Gate-Drain Charge	Q_{gd}		—	0.63	—		
Switching time	Turn-on time	t_{on}	$V_{DD} = 10 \text{ V}, I_D = 200 \text{ mA}$ $V_{GS} = 0 \text{ to } 2.5 \text{ V}, R_G = 50 \Omega$	—	30	—	ns
	Turn-off time	t_{off}		—	75	—	
Drain-source forward voltage	V_{DSF}	$I_D = -0.5 \text{ A}, V_{GS} = 0 \text{ V}$ (Note2)	—	-0.88	-1.2	V	

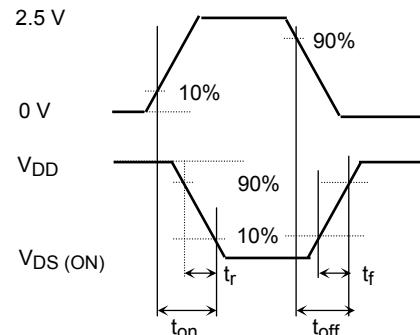
Note2: Pulse test

Switching Time Test Circuit

(a) Test Circuit



(b) V_{IN}



(c) V_{OUT}

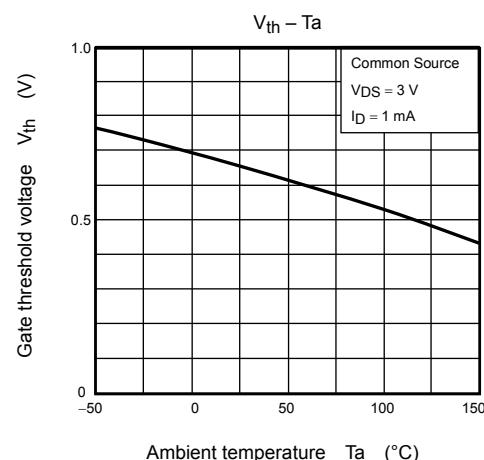
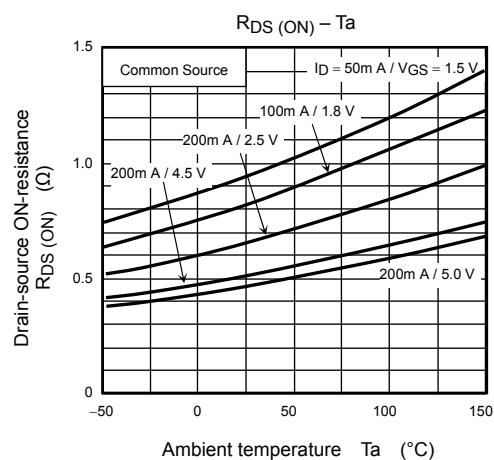
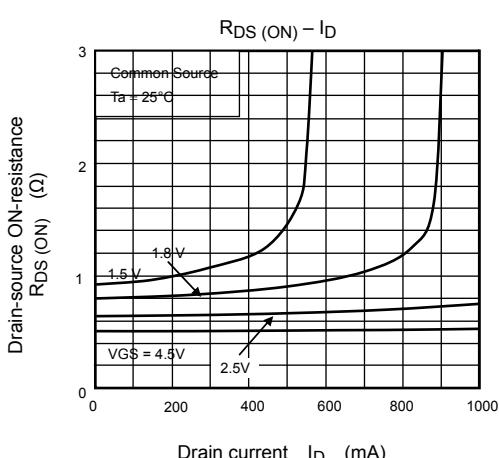
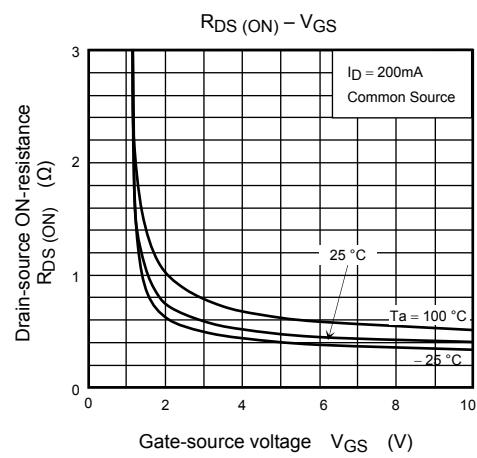
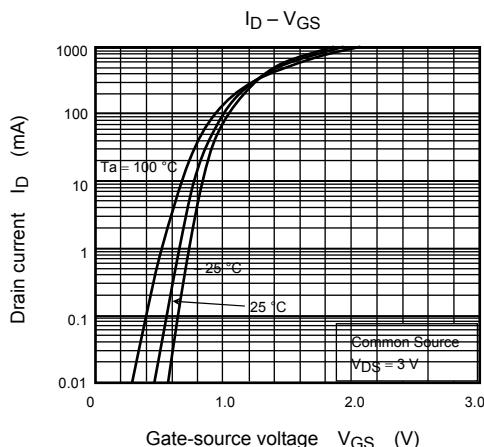
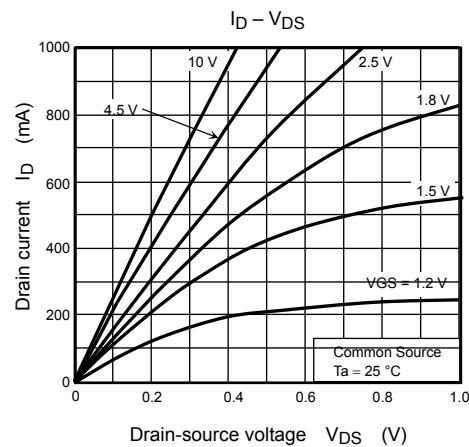


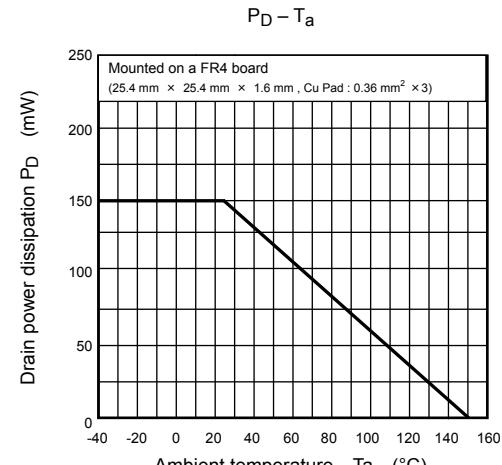
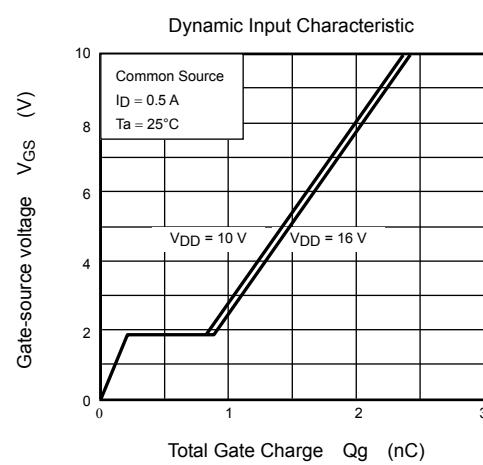
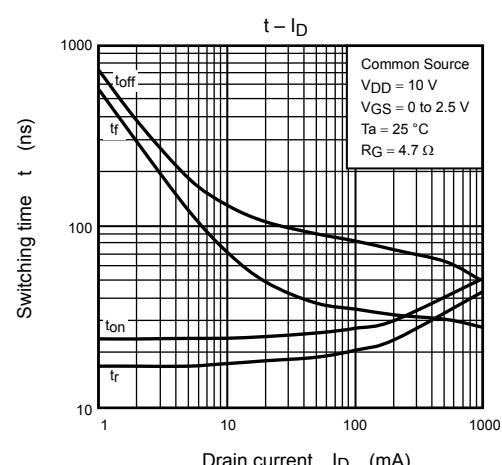
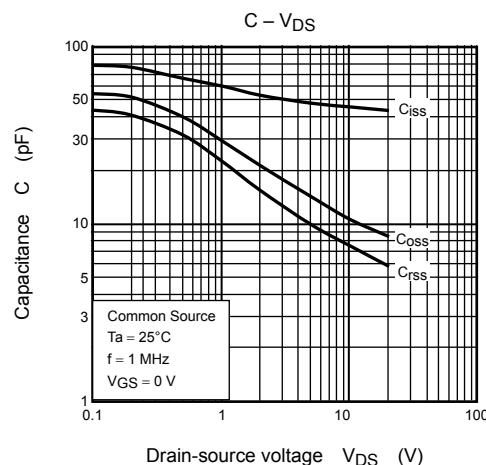
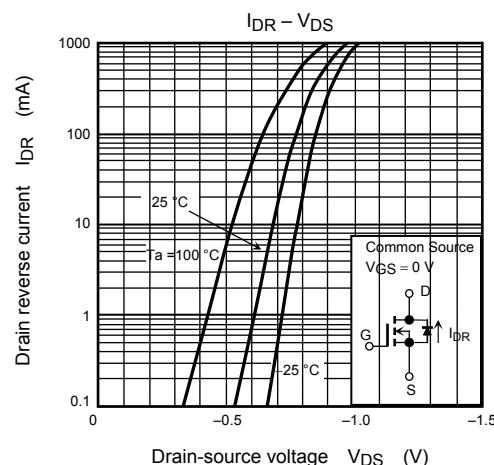
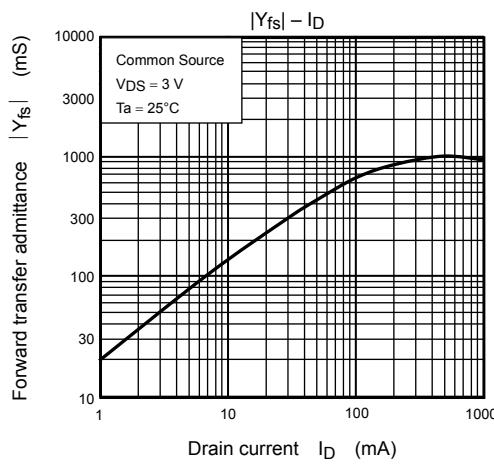
Usage Considerations

Let V_{th} be the voltage applied between gate and source that causes the drain current (I_D) to below (1 mA for the SSM3K36FS). Then, for normal switching operation, $V_{GS(on)}$ must be higher than V_{th} , and $V_{GS(off)}$ must be lower than V_{th} . This relationship can be expressed as: $V_{GS(off)} < V_{th} < V_{GS(on)}$. Take this into consideration when using the device.

Handling Precaution

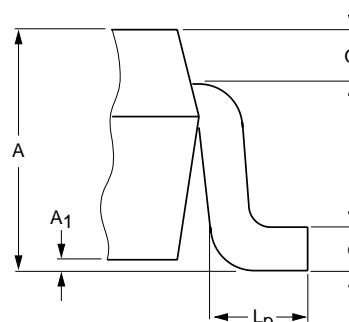
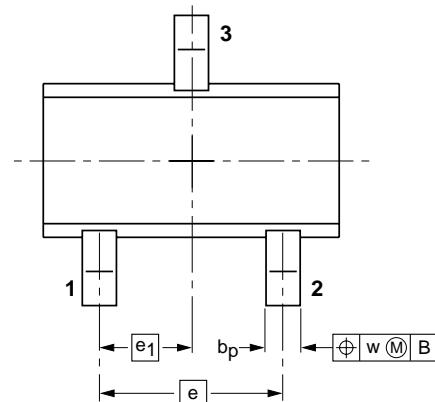
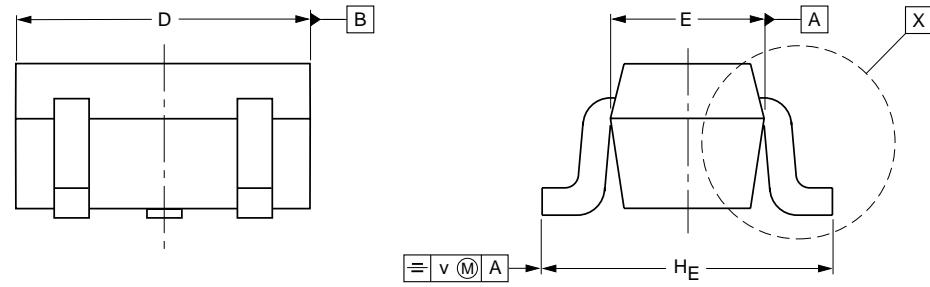
When handling individual devices that are not yet mounted on a circuit board, make sure that the environment is protected against electrostatic discharge. Operators should wear antistatic clothing, and containers and other objects that come into direct contact with devices should be made of antistatic materials.





Package Outline

SOT-523



0 0.5 1 mm
scale

DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w
mm	0.95 0.60	0.1	0.30 0.15	0.25 0.10	1.8 1.4	0.9 0.7	1	0.5	1.75 1.45	0.45 0.15	0.23 0.13	0.2	0.2

Summary of Packing Options

Package	Packing Description	Packing Quantity	Industry Standard
SOT-523	Tape/Reel,7"reel	3000	EIA-481-1